

# NPN SILICON RF POWER TRANSISTOR

**DESCRIPTION:**

The **ASI OSC-0.7L** is Designed for General Purpose Oscillator Applications up to 1.68 GHz.

**FEATURES:**

- $V_{CC} = 18\text{ V}$
- **Omnigold™** Metalization System

**MAXIMUM RATINGS**

$I_C$	150 mA
$V_{CB}$	40 V
$P_{DISS}$	7.0 W @ $T_C = 25\text{ }^\circ\text{C}$
$T_J$	-65 $^\circ\text{C}$ to +200 $^\circ\text{C}$
$T_{STG}$	-65 $^\circ\text{C}$ to +200 $^\circ\text{C}$
$\theta_{JC}$	25 $^\circ\text{C/W}$

**PACKAGE STYLE TO-46**

**ORDER CODE: ASI10637**

**CHARACTERISTICS**  $T_C = 25\text{ }^\circ\text{C}$ 

SYMBOL	TEST CONDITIONS			MINIMUM	TYPICAL	MAXIMUM	UNITS
$BV_{CEO}$	$I_C = 1.0\text{ mA}$			20			V
$BV_{CBO}$	$I_C = 100\text{ }\mu\text{A}$			40			V
$BV_{EBO}$	$I_E = 100\text{ }\mu\text{A}$			3.0			V
$I_{CBO}$	$V_{CB} = 18\text{ V}$					100	$\mu\text{A}$
$h_{FE}$	$V_{CE} = 5.0\text{ V}$	$I_C = 100\text{ mA}$		25		250	---
$C_{OB}$	$V_{CB} = 18\text{ V}$	$f = 1.0\text{ MHz}$				5.0	pF
$\eta_C$	$V_{CC} = 18\text{ V}$	$P_{OUT} = 0.7\text{ W}$	$f = 1.68\text{ GHz}$		25		%
$f_t$	$V_{CE} = 10\text{ V}$	$I_E = 100\text{ mA}$	$f = 200\text{ MHz}$		2,500		MHz
$P_{OSC}$	$V_{CC} = 18\text{ V}$	$I_E = 150\text{ mA}$	$f = 1.68\text{ GHz}$		700		mW